

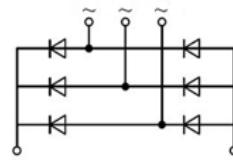
# JSD200/16S

## Description

- 1) Low forward voltage and leakage current
- 2) Low inductance package
- 3) High surge current capability



D2



symbol

**Absolute Maximum Ratings** (Packaged into D2, unless otherwise specified,  $T_{CASE}=25^{\circ}\text{C}$ )

Parameter	Test Conditions	Symbol	Values			Unit
			16	18	20	
Junction temperature range		$T_J$	-40~+150			°C
Storage temperature range		$T_{STG}$	-40~+125			°C
Repetitive peak reverse voltage		$V_{RRM}$	1600	1800	2000	V
Non-repetitive peak reverse voltage		$V_{RSM}$	1700	1900	2100	V
Output current	$T_C=95^{\circ}\text{C}$	$I_D$	200			A
Forward surge current	1/2 cycle, Sine wave	$I_{FSM}$	2000			A
Value for fusing	50Hz, $T_J=25^{\circ}\text{C}$	$I^2t$	20000			$\text{A}^2\text{s}$
RMS isolation voltage	A.C 50Hz(1s/1min)	$V_{isol}$	3600/3000			V

**Electrical Characteristics** (Packaged into D2, unless otherwise specified,  $T_{CASE}=25^{\circ}\text{C}$ )

Parameter	Test Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	$I_F=200\text{A}, T_J=25^{\circ}\text{C}$	$V_{FM}$	-	-	1.35	V
Reverse leakage current	$V_R=V_{RRM}, T_J=25^{\circ}\text{C}$	$I_{RRM}$	-	-	0.5	mA
	$V_R=V_{RRM}, T_J=150^{\circ}\text{C}$		-	-	10	mA
Threshold voltage	$T_J=150^{\circ}\text{C}$ , for power loss calculation only	$V_{TO}$	-	-	0.85	V
Slope resistance		$r_T$	-	-	3.8	$\text{m}\Omega$

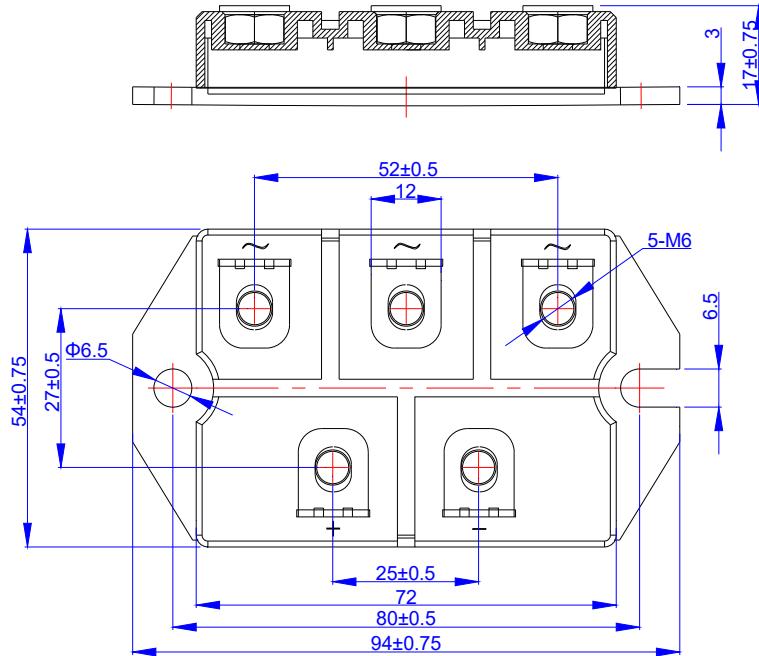
**Thermal Characteristics** (Packaged into D2, unless otherwise specified,  $T_{CASE}=25^{\circ}\text{C}$ )

Parameter	Test Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Thermal impedance(junction to case)	Per diode	$R_{th(j-c)}$	-	0.9		°C/W
Mounting torque	Module and heatsink fixed torque,screw M6	M	-	5.0	-	Nm
	Electrode connection torque, screw M6		-	5.0	-	Nm
Weight			216			g
Case style			D2			

## Ordering Information

<u>JS</u>	<u>D</u>	<u>200</u>	<u>/</u>	<u>16</u>	<u>S</u>
JieJie Semiconductor Co., Ltd					package
	Diode module		ID=200A		16: $V_{RSM} \geq 1700\text{V}$ 18: $V_{RSM} \geq 1900\text{V}$ 20: $V_{RSM} \geq 2100\text{V}$

## Mechanical Characteristics(mm)





## Three Phase Rectifier Bridge Module

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